

NTMD5838NL

Power MOSFET

40 V, 8.9 A, 25 mΩ, Dual N-Channel SO-8

Features

- Low $R_{DS(on)}$
- Low Capacitance
- Optimized Gate Charge
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DS}	40	V	
Gate-to-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JA}$ (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	7.4	A
		$T_A = 70^\circ\text{C}$	5.9	
Power Dissipation $R_{\theta JA}$ (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	2.1	W
		$T_A = 70^\circ\text{C}$	1.3	
Continuous Drain Current $R_{\theta JA}$ (Note 1)	$t \leq 10$ s	$T_A = 25^\circ\text{C}$	8.9	A
		$T_A = 70^\circ\text{C}$	7.1	
Power Dissipation $R_{\theta JA}$ (Note 1)	$t \leq 10$ s	$T_A = 25^\circ\text{C}$	3.0	W
		$T_A = 70^\circ\text{C}$	1.9	
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	35	A
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$	
Source Current (Body Diode)	I_S	7.0	A	
Single Pulse Drain-to-Source Avalanche Energy ($L = 0.1$ mH)	EAS	20	mJ	
	IAS	21	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Ambient Steady State (Notes 1 & 3)	$R_{\theta JA}$	58	$^\circ\text{C}/\text{W}$
Junction-to-Ambient - $t \leq 10$ s (Note 1)	$R_{\theta JA}$	40	
Junction-to-Ambient Steady State (Note 2)	$R_{\theta JA}$	106	

1. Surface-mounted on FR4 board using 1 sq-in pad (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using 0.155 in sq (100mm²) pad size.
3. Both channels receive equivalent power dissipation
1 W applied on each channel: $T_J = 2 \text{ W} * 58^\circ\text{C}/\text{W} + 25^\circ\text{C} = 141^\circ\text{C}$

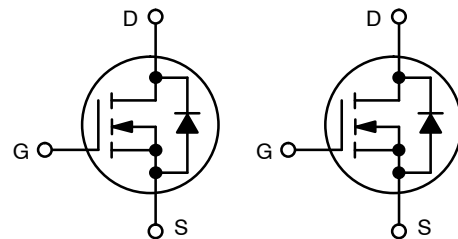


ON Semiconductor®

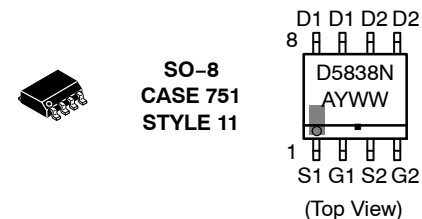
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	$I_D MAX$
40 V	25 mΩ @ 10 V	8.9 A
	30.8 mΩ @ 4.5 V	

N-CHANNEL MOSFET



MARKING DIAGRAM/ PIN ASSIGNMENT



- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTMD5838NLR2G	SO-8 (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			32		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1.0	1.8	3.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			6.0		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 7\text{ A}$		20.5	25	$\text{m}\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 7\text{ A}$		25.0	30.8	
Forward Transconductance	g_{FS}	$V_{DS} = 15\text{ V}, I_D = 7\text{ A}$		4.0		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 20\text{ V}$		785		pF
Output Capacitance	C_{OSS}			123		
Reverse Transfer Capacitance	C_{RSS}			90		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 20\text{ V}; I_D = 7\text{ A}$		17		nC
				8.6	11	
Threshold Gate Charge	$Q_{G(TH)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 20\text{ V}; I_D = 7\text{ A}$		0.8		
Gate-to-Source Charge	Q_{GS}			2.8		
Gate-to-Drain Charge	Q_{GD}			4.0		
Plateau Voltage	V_{GP}			3.2		V
Gate Resistance	R_G			1.8		Ω

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 20\text{ V}, I_D = 7\text{ A}, R_G = 2.5\ \Omega$		11		ns
Rise Time	t_r			23		
Turn-Off Delay Time	$t_{d(OFF)}$			17		
Fall Time	t_f			4.0		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 7\text{ A}$	$T_J = 25^\circ\text{C}$		0.84	1.2	V
			$T_J = 125^\circ\text{C}$		0.7		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 7\text{ A}$		17		ns	
Charge Time	t_a			11			
Discharge Time	t_b			6.0			
Reverse Recovery Charge	Q_{RR}			10			nC

4. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
5. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

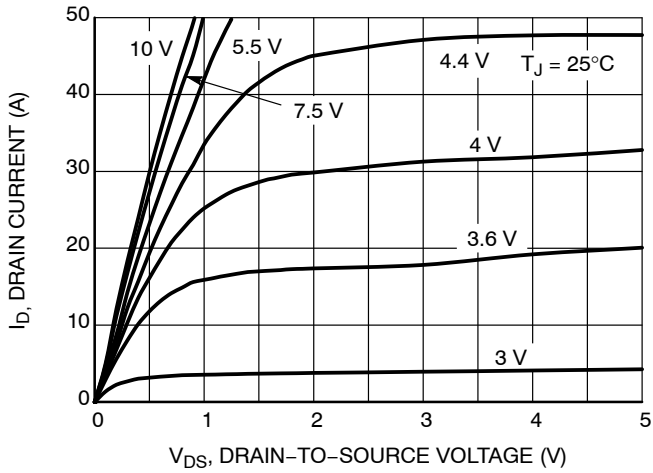


Figure 1. On-Region Characteristics

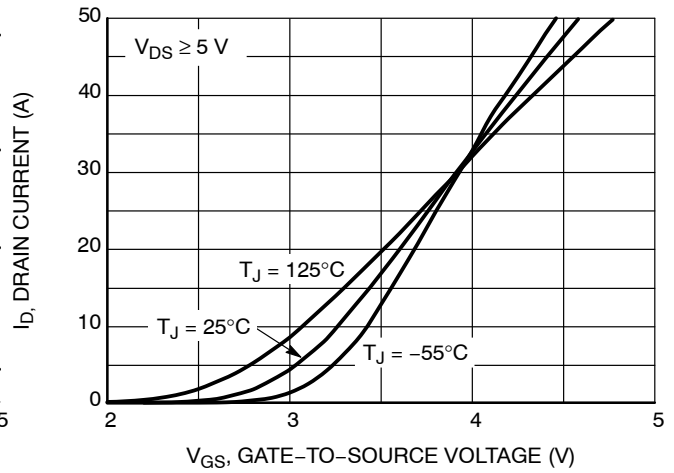


Figure 2. Transfer Characteristics

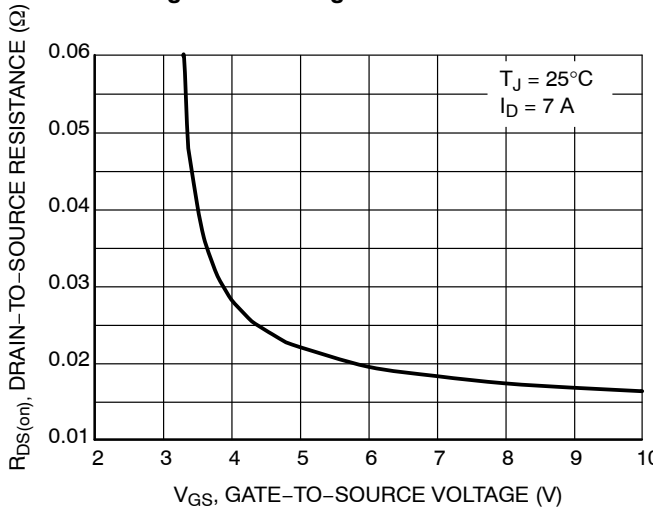


Figure 3. On-Resistance vs. Gate-to-Source Voltage

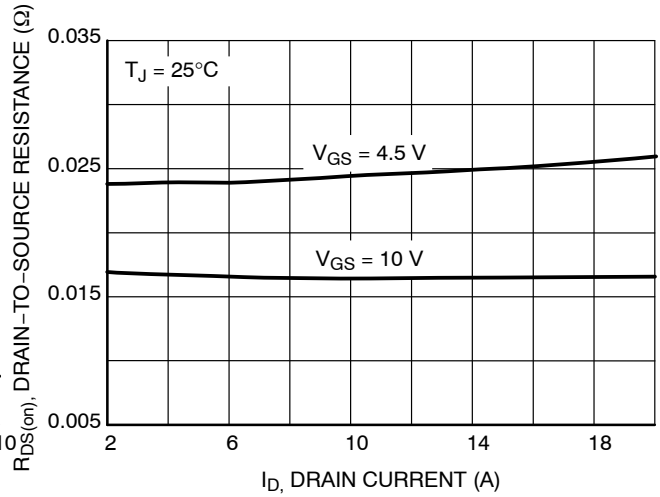


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

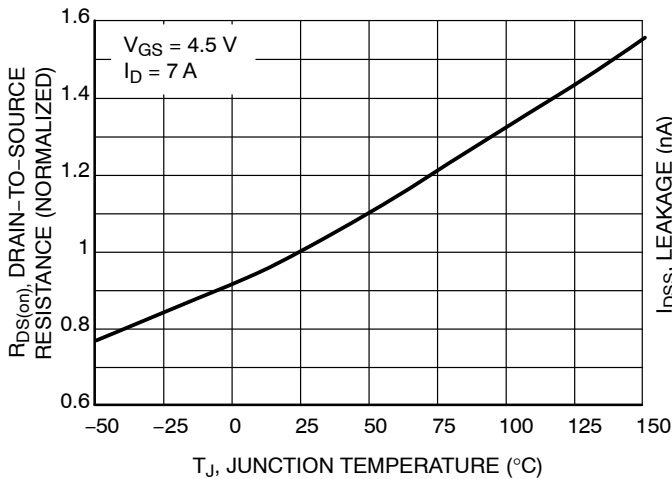


Figure 5. On-Resistance Variation with Temperature

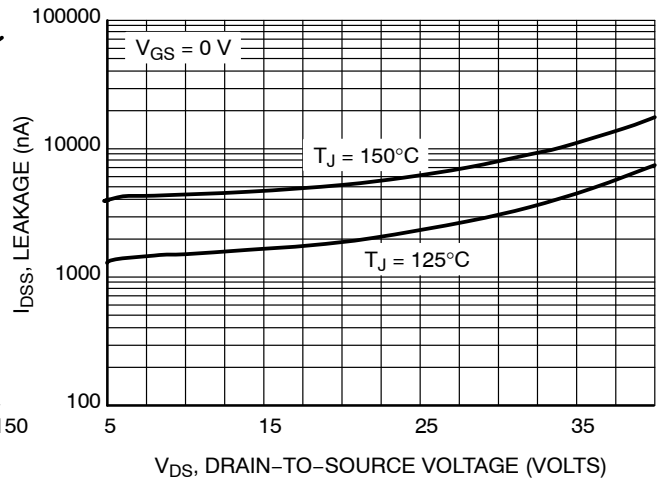


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

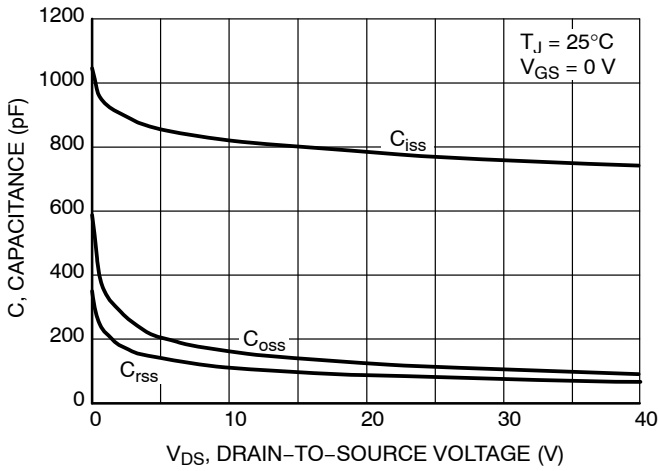


Figure 7. Capacitance Variation

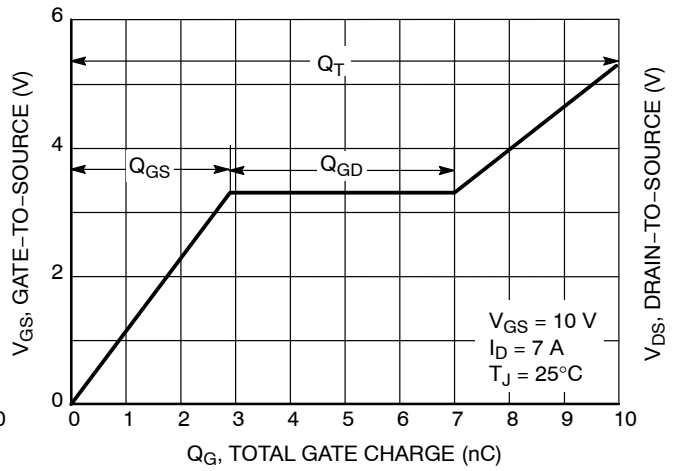


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

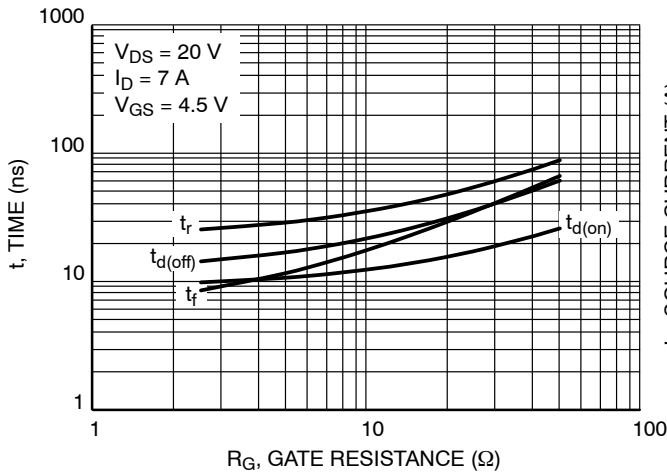


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

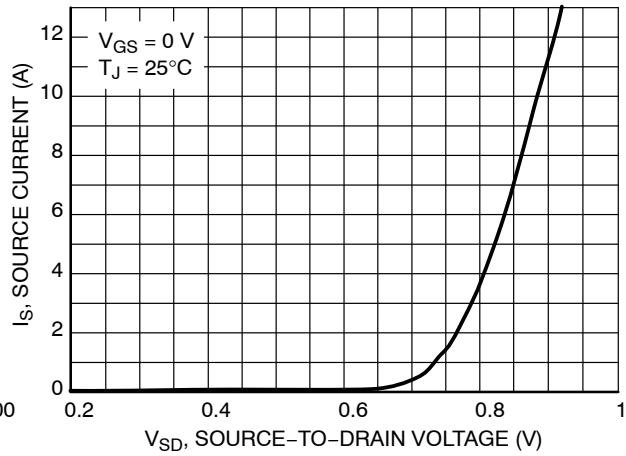


Figure 10. Diode Forward Voltage vs. Current

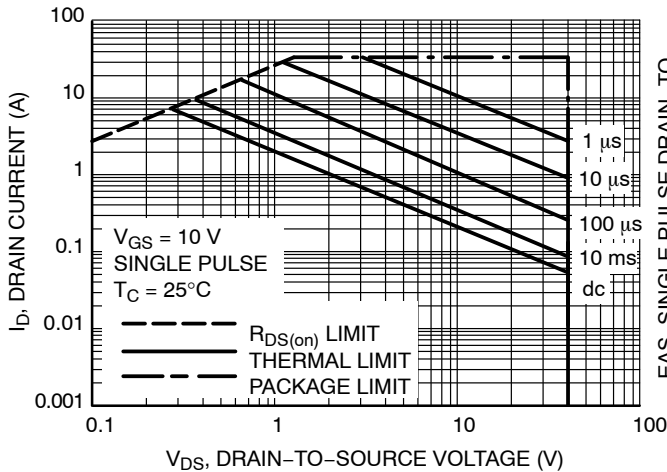


Figure 11. Maximum Rated Forward Biased Safe Operating Area

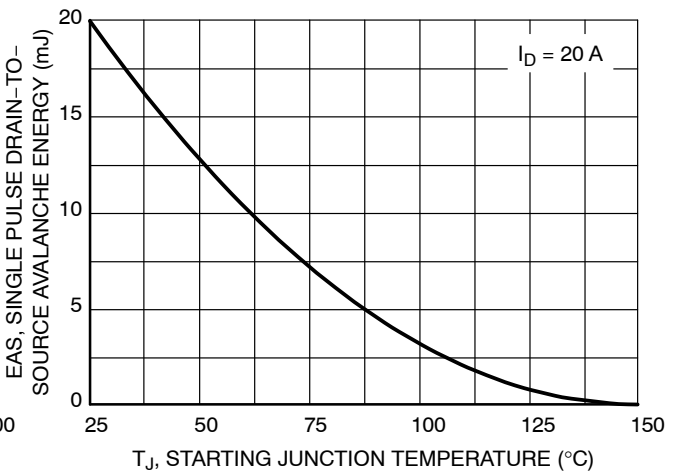


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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TYPICAL PERFORMANCE CURVES

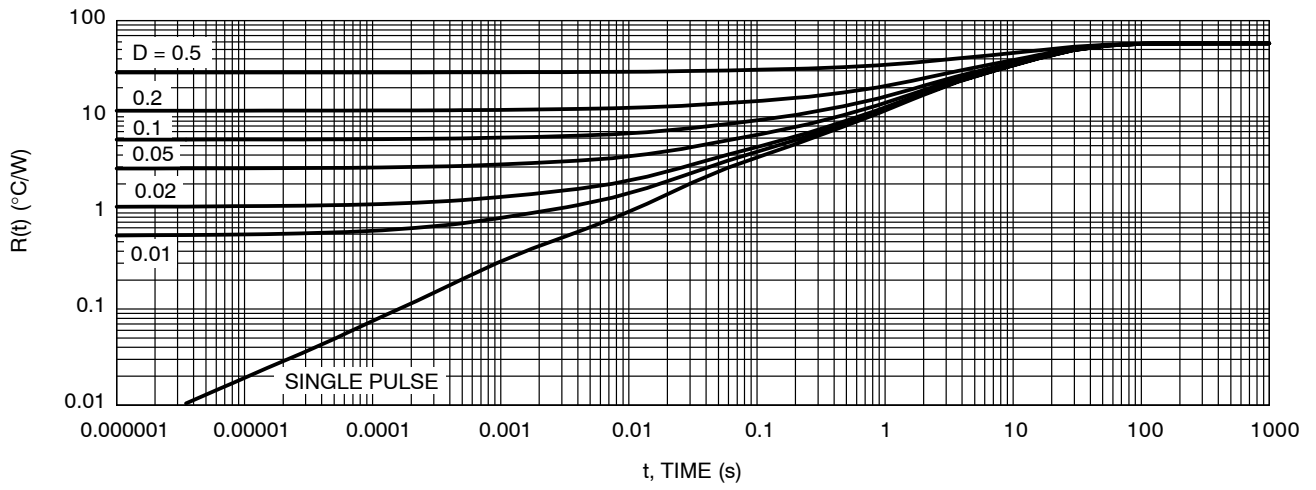
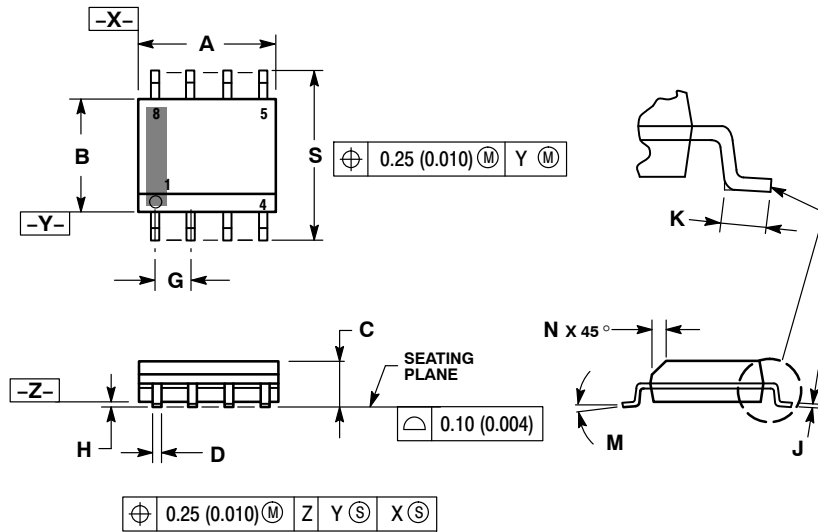


Figure 13. Thermal Response

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PACKAGE DIMENSIONS

SOIC-8 NB
CASE 751-07
ISSUE AK

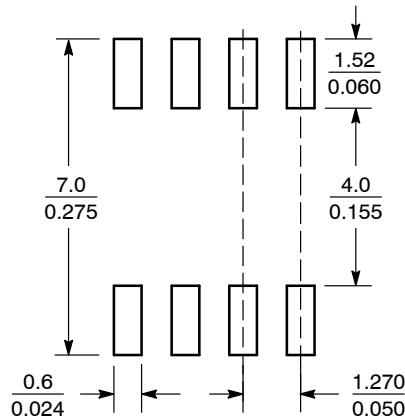


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



SCALE 6:1 (mm/inches)

STYLE 11:

1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 1
7. DRAIN 1
8. DRAIN 1

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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